



H02N60 Series

N-Channel Power Field Effect Transistor

Description

This high voltage MOSFET uses an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain-to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

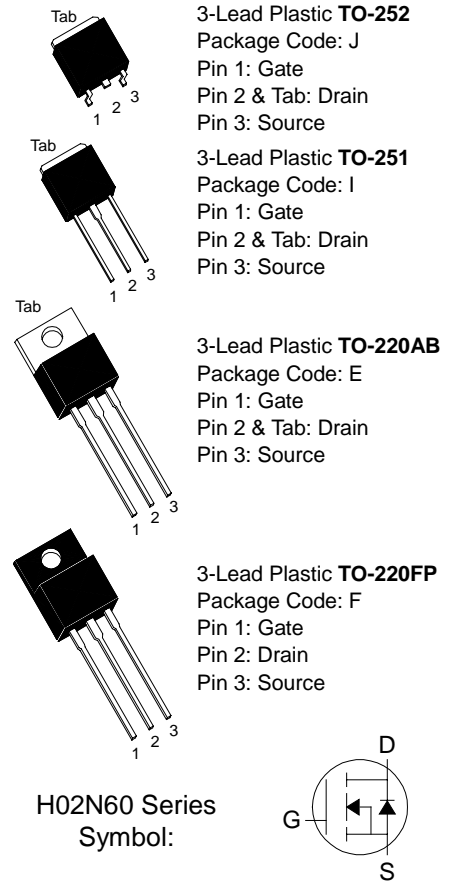
Features

- Robust High Voltage Termination
- Avalanche Energy Specified
- Source-to-Drain Diode Recovery Time Comparable to a Discrete Fast Recovery Diode
- Diode is Characterized for Use in Bridge Circuits
- I_{DSS} and $V_{DS(on)}$ Specified at Elevated Temperature

Absolute Maximum Ratings

Symbol	Parameter	Value	Units
I_D	Drain to Current (Continuous)	2	A
I_{DM}	Drain to Current (Pulsed)	8	A
V_{GS}	Gate-to-Source Voltage (Continue)	± 20	V
P_D	Total Power Dissipation ($T_C=25^\circ\text{C}$) H02N60I (TO-251) / H02N60J (TO-252)	50	W
	H02N60E (TO-220AB)	50	
	H02N60F (TO-220FP)	25	
	Derate above 25°C H02N60I (TO-251) / H02N60J (TO-252)	0.4	
	H02N60E (TO-220AB)	0.4	$\text{W}/^\circ\text{C}$
	H02N60F (TO-220FP)	0.33	
T_j, T_{stg}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
E_{AS}	Single Pulse Drain-to-Source Avalanche Energy- $T_j=25^\circ\text{C}$ ($V_{DD}=100\text{V}$, $V_{GS}=10\text{V}$, $I_L=2\text{A}$, $L=10\text{mH}$, $R_G=25\Omega$)	35	mJ
T_L	Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds	260	$^\circ\text{C}$

H02N60 Series Pin Assignment





Thermal Characteristics

Symbol	Parameter	Value		Units
$R_{\theta JC}$	Thermal Resistance Junction to Case Max.	TO-251 / TO-252	2	°C/W
		TO-220AB	2	
		TO-220FP	3.3	
$R_{\theta JA}$	Thermal Resistance Junction to Ambient Max.	62.5		°C/W

Electrical Characteristics (T_J=25°C, unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ($V_{GS}=0V, I_D=250\mu A$)	600	-	-	V
I_{DSS}	Drain-Source Leakage Current ($V_{DS}=600V, V_{GS}=0V$)	-	-	1	μA
	Drain-Source Leakage Current ($V_{DS}=480V, V_{GS}=0V, T_J=125^\circ C$)	-	-	50	μA
I_{GSSF}	Gate-Source Leakage Current-Forward ($V_{gsf}=20V, V_{DS}=0V$)	-	-	100	nA
I_{GSSR}	Gate-Source Leakage Current-Reverse ($V_{gsr}=-20V, V_{DS}=0V$)	-	-	-100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS}=V_{GS}, I_D=250\mu A$)	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ($V_{GS}=10V, I_D=1A$)*	-	-	4.4	Ω
g_{FS}	Forward Transconductance ($V_{DS}\geq 50V, I_D=1A$)*	1	-	-	mhos
C_{iss}	Input Capacitance	-	435	-	pF
C_{oss}	Output Capacitance	$V_{GS}=0V, V_{DS}=25V, f=1MHz$		-	
C_{rss}	Reverse Transfer Capacitance	-	9.2	-	
$t_{d(on)}$	Turn-on Delay Time	-	12	-	ns
t_r	Rise Time	$(V_{DD}=300V, I_D=2A, R_G=18\Omega, V_{GS}=10V)^*$		-	
$t_{d(off)}$	Turn-off Delay Time	-	30	-	
t_f	Fall Time	-	24	-	
Q_g	Total Gate Charge	-	13	22	nC
Q_{gs}	Gate-Source Charge	$(V_{DS}=300V, I_D=6A, V_{GS}=10V)^*$		-	
Q_{gd}	Gate-Drain Charge	-	6	-	
L_D	Internal Drain Inductance (Measured from the drain lead 0.25" from package to center of die)	-	4.5	-	nH
L_S	Internal Drain Inductance (Measured from the drain lead 0.25" from package to source bond pad)	-	7.5	-	nH

*: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Source-Drain Diode

Symbol	Characteristic		Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage(1)	$I_S=2A, V_{GS}=0V, T_J=25^\circ C$	-	-	1.6	V
t_{on}	Forward Turn-On Time	$I_S=2A, V_{GS}=0V, d_{IS}/d_t=100A/\mu s$	-	**	-	ns
t_{rr}	Reverse Recovery Time		-	340	-	ns

** : Negligible, Dominated by circuit inductance



TO-252 Dimension

3-Lead TO-252 Plastic
Surface Mount Package
HSMC Package Code: J

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.35	6.80
C	4.80	5.50
F	1.30	1.70
G	5.40	6.25
H	2.20	3.00
L	0.40	0.90
M	2.20	2.40
N	0.90	1.50
a1	0.40	0.65
a2	-	*2.30
a5	0.65	1.05

*: Typical, Unit: mm

3-Lead TO-252 Plastic
Surface Mount Package
HSMC Package Code: J

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.40	6.80
B	-	6.00
C	5.04	5.64
D	-	*4.34
E	0.40	0.80
F	0.50	0.90
G	5.90	6.30
H	2.50	2.90
I	9.20	9.80
J	0.60	1.00
K	-	0.96
L	0.66	0.86
M	2.20	2.40
N	0.70	1.10
O	0.82	1.22
a1	0.40	0.60
a2	2.10	2.50
y1	-	5°
y2	-	3°

*: Typical, Unit: mm



TO-251 Dimension

Diagram showing top and side views of a 3-lead TO-251 plastic package. Dimensions include A (width), C (lead spacing), F (tab height), G (package height), H1 (lead height), K (lead diameter), K1 (lead diameter), L (lead diameter), M (lead length), and a2 (lead width).

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

0 2 N 6 0

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.35	6.80
C	4.80	5.50
F	1.30	1.70
G	5.40	6.25
H1	6.75	8.00
K	0.50	0.90
K1	0.40	0.90
L	0.90	1.50
M	2.20	2.40
a1	0.40	0.65
a2	-	*2.30

*: Typical, Unit: mm

3-Lead TO-251 Plastic Package
HSMC Package Code: I

Diagram showing top, side, and bottom views of a 3-lead TO-251 plastic package. Dimensions include A, B, C, D, E, F, G, H, H1, J, K, K1, M, y1, y2, and a1/a2.

Marking:

Pb Free Mark
 Pb-Free: "●" (Note)
 Normal: None

0 2 N 6 0

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.40	6.80
B	-	6.00
C	5.04	5.64
D	-	*4.34
E	0.40	0.80
F	0.50	0.90
G	5.90	6.30
H	-	*1.80
H1	-	*9.30
I	-	*16.10
J	-	*0.80
K	-	0.96
K1	-	*0.76
M	2.20	2.40
a1	0.40	0.60
a2	2.10	2.50
y1	-	5°
y2	-	3°

*: Typical, Unit: mm

3-Lead TO-251 Plastic Package
HSMC Package Code: I



TO-220AB Dimension

3-Lead TO-220AB
Plastic Package
HSMC Package Code: E

Marking:

Pb Free Mark
Pb-Free: "●" (Note)
Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2 & Tab.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	5.58	7.49
B	8.38	8.90
C	4.40	4.70
D	1.15	1.39
E	0.35	0.60
F	2.03	2.92
G	9.66	10.28
H	-	*16.25
I	-	*3.83
J	3.00	4.00
K	0.75	0.95
L	2.54	3.42
M	1.14	1.40
N	-	*2.54
O	12.70	14.27
P	14.48	15.87

*: Typical, Unit: mm

TO-220FP Dimension

3-Lead TO-220FP
Plastic Package
HSMC Package Code: F

Marking:

Pb Free Mark
Pb-Free: "●" (Note)
Normal: None

Date Code Control Code

Note: Green label is used for pb-free packing

Pin Style: 1.Gate 2.Drain 3.Source

Material:

- Lead solder plating: Sn60/Pb40 (Normal), Sn/3.0Ag/0.5Cu or Pure-Tin (Pb-free)
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0

DIM	Min.	Max.
A	6.48	7.40
C	4.40	4.90
D	2.34	3.00
E	0.45	0.80
F	9.80	10.36
G	3.10	3.60
I	2.70	3.43
J	0.60	1.00
K	2.34	2.74
L	12.48	13.60
M	15.67	16.20
N	0.90	1.47
O	2.00	2.96
$\alpha 1/2/4/5$	-	*5°
$\alpha 3$	-	*27°

*: Typical, Unit: mm

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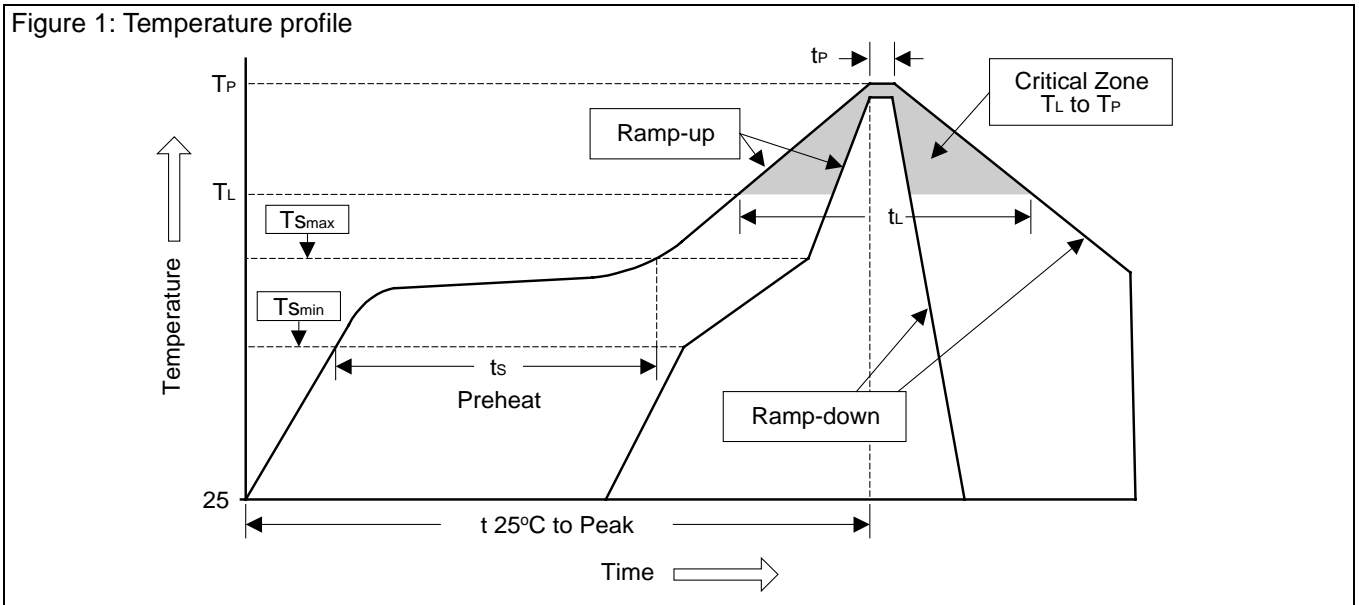
Head Office And Factory:

- **Head Office** (Hi-Sincerity Microelectronics Corp.): 10F.,No. 61, Sec. 2, Chung-Shan N. Rd. Taipei Taiwan R.O.C.
Tel: 886-2-25212056 Fax: 886-2-25632712, 25368454
- **Factory 1:** No. 38, Kuang Fu S. Rd., Fu-Kou Hsin-Chu Industrial Park Hsin-Chu Taiwan. R.O.C
Tel: 886-3-5983621~5 Fax: 886-3-5982931



Soldering Methods for HSMC's Products

1. Storage environment: Temperature=10°C~35°C Humidity=65%±15%
2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (T _{Smin})	100°C	150°C
- Temperature Max (T _{Smax})	150°C	200°C
- Time (min to max) (ts)	60~120 sec	60~180 sec
T _{Smax} to T _L		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T _L)	183°C	217°C
- Time (t _L)	60~150 sec	60~150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak Temperature (t _p)	10~30 sec	20~40 sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak temperature	Dipping time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec